FLAT-BASE TYPE INSULATED TYPE

PS12012-A



INTEGRATED FUNCTIONS AND FEATURES

- 3-Phase IGBT inverter bridge configured by the latest 3rd. generation IGBT and diode technologies.
- · Circuit for dynamic braking of motor regenerative energy.
- Inverter output current capability Io (Note 1):

Type Name	100% load	150% over load
PS12012-A	1.2A (rms)	1.8A (rms), 1min

(Note 1) : The inverter output current is assumed to be sinusoidal and the peak current value of each of the above loading cases is defined as : $lop = lo \times \sqrt{2}$

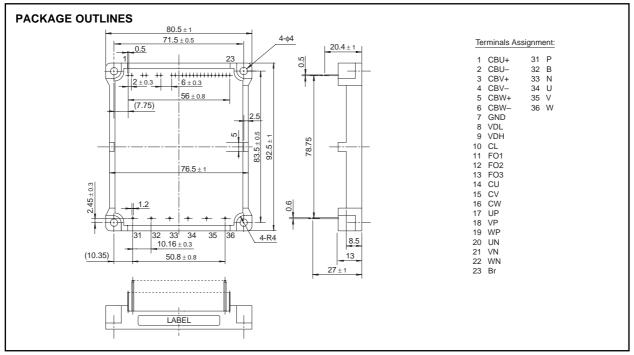
INTEGRATED DRIVE, PROTECTION AND SYSTEM CONTROL FUNCTIONS:

- For P-Side IGBTs: Drive circuit, High-speed photo-couplers, Short circuit protection (SC),

 Bootstrap circuit supply scheme (Single drive power supply) and Under-voltage protection (UV).
- For N-Side IGBTs: Drive circuit, Short-circuit protection (SC), Control supply Under voltage and Over voltage protection (OV/UV), System Over temperature protection (OT), Fault output signaling circuit (Fo), and Current-Limit warning signal output (CL).
- For Brake circuit IGBT : Drive circuit.
- · Warning and Fault signaling :
 - Fo1: Short circuit protection for lower-leg IGBTs and Input interlocking against spurious arm shoot-through.
 - Fo2: N-side control supply abnormality locking (OV/UV)
 - Fo3: System over-temperature protection (OT).
 - CL: Warning for inverter current overload condition
- For system feedback control: Analogue signal feedback reproducing actual inverter output phase current (36).
- Input Interface : 5V CMOS/TTL compatible, Schmitt trigger input, and Arm-Shoot-Through interlock protection

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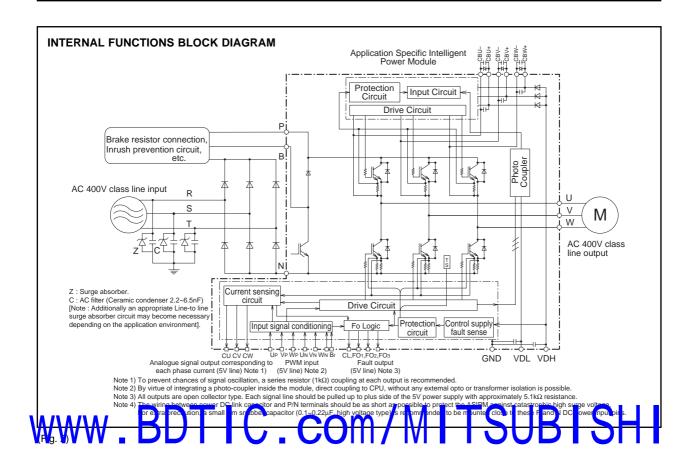
Acoustic noise-less 0.2kW/AC400V Class 3 Phase inverter and other motor control applications.



(Fig. 1)



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MAXIMUM RATINGS (Tj = 25°C) INVERTER PART (Including Brake Part)

Symbol	Item	Condition	Ratings	Unit
Vcc	Supply voltage	Applied between P-N	900	V
VCC(surge)	Supply voltage (surge)	Applied between P-N, Surge-value	1000	V
VP or VN	Each output IGBT collector-emitter static voltage	Applied between P-U, V, W, Br or U, V, W, Br-N	1200	V
VP(S) or VN(S)	Each output IGBT collector-emitter surge voltage	Applied between P-U, V, W, Br or U, V, W, Br-N	1200	V
±lc(±lcp)	Each output IGBT collector current	Tc = 25°C	±5 (±10)	Α
lc(lcp)	Brake IGBT collector current		5 (10)	Α
IF(IFP)	Brake diode anode current	Note : "()" means Ic peak value	5 (10)	Α

CONTROL PART

Symbol	Item	Item Condition		Unit
VDH, VDB	Supply voltage	Applied between VDH-GND, CBU+-CBU-, CBV+-CBV-, CBW+-CBW-	20	V
VDL	Supply voltage	Applied between VDL-GND	7	V
VCIN	Input signal voltage	Applied between UP · VP · WP · UN · VN · WN · Br-GND	-0.5 ~ VDL+0.5	V
VFO	Fault output supply voltage	Applied between Fo1 · Fo2 · Fo3-GND	− 0.5 ~ 7	V
IFO	Fault output current	Sink current of F01 · F02 · F03	15	mA
VCL	Current-limit warning output voltage	Applied between CL-GND	− 0.5 ~ 7	V
ICL	CL output current	Sink current of CL	15	mA
Ico	Analogue-current-signal output current	Sink current of CU · CV · CW	±1	mA



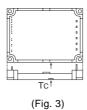
FLAT-BASE TYPE INSULATED TYPE

TOTAL SYSTEM

Symbol	Item	Condition	Ratings	Unit
Tj	Junction temperature	(Note 2)	−20 ~ +125	°C
Tstg	Storage temperature	_	−40 ~ +125	°C
Tc	Module case operating temperature	(Fig. 3)	−20 ~ +100	°C
Viso	Isolation voltage	60 Hz sinusoidal AC for 1 minute, between all terminals and base plate.	2500	Vrms
_	Mounting torque	Mounting screw: M3.5	0.78 ~ 1.27	N⋅m

Note 2): The item defines the maximum junction temperature for the power elements (IGBT/Diode) of the ASIPM to ensure safe operation. However, these power elements can endure instantaneous junction temperature as high as 150°C. To make use of this additional temperature allowance, a detailed study of the exact application conditions is required and, accordingly, necessary information is to be provided before use.

CASE TEMPERATURE MEASUREMENT POINT (3mm from the base surface)



THERMAL RESISTANCE

Sumbol Itom		Condition	Ratings			Unit
Symbol	Item	Condition	Min.	Тур.	Max.	Unit
Rth(jc)Q		In er er IGBT (1/6)			5.0	°C/W
Rrh(p)A	Junction to calle Thermal	Ir verter FWD (1/6)		K	7.5	-C/W
Flith(ju) (3)	Resistance	Bit IGET				°C/W
Rth(jc)FB		Brake FWDi	_	_	7.3	°C/W
Rth(c-f)	Contact Thermal Resistance	Contact Thermal Resistance Case to fin, thermal grease applied (1 Module)				

ELECTRICAL CHARACTERISTICS (Tj = 25°C, VDH = 15V, VDB = 15V, VDL = 5V unless otherwise noted)

Cumbal	14	Condition		Ratings		
Symbol	Item	Condition	Min.	Тур.	Max.	Unit
VCE(sat)	Collector-emitter saturation voltage	VDL = 5V, VDH = VDB = 15V Input = ON, Tj = 25°C, Ic = 5A	_	_	3.6	V
VEC	FWDi forward voltage	Tj = 25° C, Ic = -5 A, Input = OFF	_	_	3.5	V
VCE(sat)Br	Brake IGBT Collector-emitter saturation voltage	VDL = 5V, VDH = 15V Input = ON, Tj = 25°C, Ic = 5A	_	_	3.6	V
VFBr	Brake diode forward voltage	Tj = 25°C, IF = 5A, Input = OFF	_	_	3.5	V
ton		1/2 Bridge inductive, Input = ON	0.3	1.2	2.0	μs
tc(on)	Switching times	Vcc = 600V, Ic = 5A, Tj = 125°C	_	0.5	1.4	μs
toff	Switching times	VDL = 5V, VDH = 15V, VDB = 15V	_	2.2	4.0	μs
tc(off)		Note : ton, toff include delay time of the internal control circuit.		0.9	1.6	μs
trr	FWD reverse recovery time			0.2	_	μs
	Short circuit endurance (Output, Arm, and Load, Short Circuit Modes)	$\label{eq:controller} \begin{array}{ll} \text{Vcc} \leq 800\text{V}, \text{ Input} = \text{ON (One-Shot)} \\ \text{Tj} = 125^{\circ}\text{C start} \\ \text{13.5V} \leq \text{VDH} = \text{VDB} = \leq 16.5\text{V} \\ \end{array}$				
	Switching SOA	Vcc ≤ 800V, Tj ≤ 125°C,	No destruction			
	Switching SOA	Ic < IoL(CL) operation level, Input = ON, $13.5V \le VDH = VDB = \le 16.5V$	No protecting operationNo Fo output			
IDН	VDH Circuit Current	VDL = 5V, VDH = 15V, VCIN = 5V			150	mA
IDL	VDL Circuit Current	VDL = 5V, VDH = 15V, VCIN = 5V	_	_	50	mA
Vth(on)	Input on threshold voltage		0.8	1.4	2.0	V
Vth(off)	Input off threshold voltage		2.5	3.0	4.0	V
Ri	Input pull-up resistor Integrated between input terminal-VDH		_	150	_	kΩ



FLAT-BASE TYPE INSULATED TYPE

ELECTRICAL CHARACTERISTICS (Tj = 25°C, VDH = 15V, VDB = 15V, VDL = 5V unless otherwise noted)

Symbol	Item				Condition			Ratings		Unit
Symbol	ne	#111			Condition		Min.	Тур.	Max.	Offic
fPWM	PWM input frequency		Tc ≤ 100°C, Tj ≤ 125°C		2	_	15	kHz		
txx	Allowable input on-pulse width		VDH = 15V, VDL =	$= 5V, TC = -20^{\circ}C \sim +100^{\circ}C$	Note 3)	2	_	500	μs	
tdead	Allowable input s for blocking arm			Relates to corres	ponding inputs (Except brake 00°C	e part)	4.0	_	_	μs
tint	Input inter-lock	sensin	g	Relates to corres	ponding inputs (Except brake	e part)		65	100	ns
Vco				Ic = 0A	VDH = 15V		1.87	2.27	2.57	V
VC+(200%)	Analogue signa	al linea	rity with	Ic = IOP(200%)	VDL = 5V		0.77	1.17	1.47	V
VC-(200%)	output current			Ic = -IOP(200%)	Tc = -20 ~ 100°C	(Fig.4)	2.97	3.37	3.67	V
ΔVco	Offset change are	a vs ten	nperature	VDH = 15V, VDL =	5V, Tc = -20 ~ 100°C		_	15	_	mV
VC+			r :	Ic > IOP(200%), VD	рн = 15V,		_	_	0.7	V
Vc-	Analogue signal ou	itput voit	age limit	VDL = 5V		(Fig. 4)	4.0	_	_	V
ΔVC(200%)	Analogue signal overall linear variation		all linear	VCO-VC±(200%)			_	1.1	_	V
rCH	Analogue signal data hold accuracy		Correspond to m Ic = IOP(200%)	ax. 500μs data hold period o	nly, (Fig. 5)	-5	_	5	%	
td(read)	Analogue signal reading time		ng time	After input signal	trigger point	(Fig. 8)	_	3	_	μs
ICL(H)	Signal output cur- Idle		Idle	On an application of	- m.u.t			_	1	μΑ
ICL(L)	rent of CL ope	ration	Active	Open collector onput		_	1	_	mA	
±loL	CL warning ope	eration	level	VDL = 5V, VDH =	15V, TC = −20 ~ 100°C	(Note 4)	3.23	3.90	4.92	Α
SC	Short circuit cu	rrent tr	ip level	Tj = 25°C	(Fig. 7)), (Note 5)	5.7	8.0	11.6	Α
ОТ	Over tenperature	Trip	level	\/	45)/		100	110	120	°C
OTr	protection	Res	et level	VDL = 5V, VDH = 15V		_	90	_	°C	
UVDB UVD	Supply circuit		et evel le rel		C _{TC} COM/MIT			0 5 12 10	12.5 12.7	V V V
UVDHr		under and over voltage protection Reset level		- Tj ≤ 125°C		11.55	12.50	13.25	V	
OVDH	protection						18.00	19.20	20.15	V
OVDHr		Reset level					16.50	17.50	18.65	V
tdv		Filte	r time					10		μs
IFO(H)	Foult output o	ırront	Idle	Onen collecter s	itorit			_	1	μΑ
IFO(L)	Fault output cu	ment	Active	Open collector or	ııpuı		_	1	_	mA

(Note 3): (a) Allowable minimum input on-pulse width: This item applies to P-side circuit only.

(b) Allowable maximum input on-pulse width: This item applies to both P-side and N-side circuits excluding the brake circuit.

(Note4): CL output: The "current limit warning (CL) operation circuit outputs warning signal whenever the arm current exceeds this limit. The circuit is reset automatically by the next input signal and thus, it operates on a pulse-by-pulse scheme.

(Note5): The short circuit protection works instantaneously when a high short circuit current flows through an internal IGBT rising up momentarily. The protection function is, thus meant primarily to protect the ASIPM against short circuit distraction. Therefore, this function is not recommended to be used for any system load current regulation or any over load control as this might, cause a failure due to excessive temperature rise. Instead, the analogue current output feature or the over load warning feature (CL) should be appropriately used for such current regulation or over load control operation. In other words, the PWM signals to the ASIPM should be shut down, in principle, and not to be restarted before the junction temperature would recover to normal, as soon as a fault is feed back from its Fo1 pin of the ASIPM indicating a short circuit situation.

RECOMMENDED CONDITIONS

Symbol	Item Condition	Ratings			Unit	
Symbol	Item	Condition	Min.	Тур.	Max.	Unit
Vcc	Supply voltage		600	800	V	
VDH, VDB	Control supply voltage	Applied between VDH-GND, CBU+-CBU-, CBV+-CBV-, CBW+-CBW-	13.5	15.0	16.5	٧
VDL	Control supply voltage Applied between VDL-GND		4.8	5.0	5.2	V
ΔV DH, ΔV DB, ΔV DL	Supply voltage ripple		-1	_	+1	V/µs
VCIN(on)	Input ON voltage		_	_	0.3	V
VCIN(off)	Input OFF voltage		4.8	_	_	V
fPWM	PWM Input frequency Using application circuit		2	10	15	kHz
tdead	Arm shoot-through blocking time	Using application circuit	4.0	_	_	μs



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Fig. 4 OUTPUT CURRENT ANALOGUE SIGNALING LINEARITY

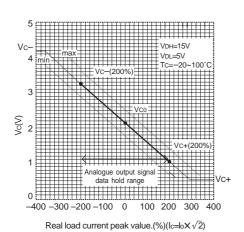
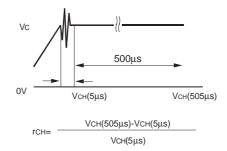
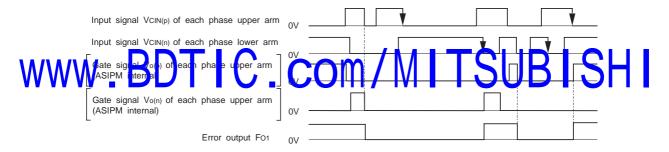


Fig. 5 OUTPUT CURRENT ANALOGUE SIGNALING "DATA HOLD" DEFINITION



Note; Ringing happens around the point where the signal output voltage changes state from "analogue" to "data hold" due to test circuit arrangement and instrumentational trouble. Therefore, the rate of change is measured at a 5 µs delayed point.

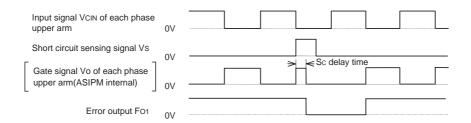
Fig. 6 INPUT INTERLOCK OPERATION TIMING CHART



Note: Input interlock protection circuit; It is operated when the input signals for any upper-arm / lower-arm pair of a phase are simultaneously in "LOW" level.

By this interlocking, both upper and lower IGBTs of this mal-triggered phase are cut off, and "Fo" signal is outputted. After an "input interlock" operation the circuit is latched. The "Fo" is reset by the high-to-low going edge of either an upper-leg, or a lower-leg input, whichever comes in later.

Fig. 7 TIMING CHART AND SHORT CIRCUIT PROTECTION OPERATION

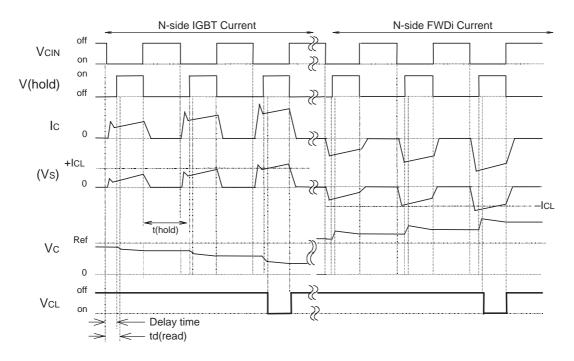


Note: Short circuit protection operation. The protection operates with "Fo" flag and reset on a pulse-by-pulse scheme. The protection by gate shutdown is given only to the IGBT that senses an overload (excluding the IGBT for the "Brake").



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Fig. 8 INVERTER OUTPUT ANALOGUE CURRENT SENSING AND SIGNALING TIMING CHART.



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Fig. 9 START-UP SEQUENCE

Normally at start-up, Fo and CL output signals will be pulled-up High to VDL voltage (OFF level); however, Fo1 output may fall to Low (ON) level at the instant of the first ON input pulse to an N-Side IGBT. This can happen particularly when the boot-strap capacitor is of large size. Fo1 resetting sequence (together with the boot-strap charging sequence) is explained in the following graph

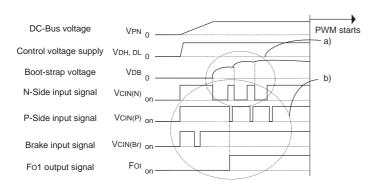
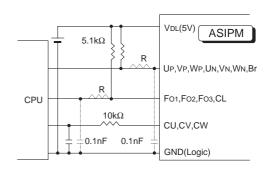


Fig. 10 RECOMMENDED I/O INTERFACE CIRCUIT



a) Boot-strap charging scheme :

Apply a train of short ON pulses at all N-IGBT input pins for adequate charging (pulse width = approx. $20\mu s$ number of pulses =10 ~ 500 depending on the boot-strap capacitor size)

b) Fo1 resetting sequence:

Apply ON signals to the following input pins : Br \rightarrow Un/Vn/Wn \rightarrow Up/Vp/Wp in that order.

